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Save online the high-quality of in the order with a 97% success rate. Please use the login below to comment on this tutorial. This login also allows you to manage your subscription settings in My Account. Simply enter your email address to the right below to login and comment on this tutorial using your free account.The present invention relates to a method for manufacturing semiconductor thin film, e.g., high-resolution thin film, by a sputtering process, particularly a method for manufacturing a semiconductor thin film including a barrier layer of metal silicide to efficiently obtain a semiconductor thin film as a device. In recent years, semiconductor thin films have been required to be thinner and higher in density, to cause a large current to flow, and to have a high electron mobility to improve the operating speed of devices. For that reason, the semiconductor thin films are desired to be deposited at a rate higher by four digits compared with the existing ones. As to the thin films used for semiconductor devices, there are provided semiconductor thin films of mainly aluminum (Al) and its alloys and silicon (Si) and its alloys by a vacuum evaporation process, and polycrystalline silicon (poly-Si) obtained by a process of depositing a CVD silicon layer on a Si substrate and crystallizing it. One example of crystallized silicon is poly-Si obtained by a technique of depositing an amorphous silicon layer on a substrate and crystallizing it by a heat treatment. Although this technique can realize a high-performance film of a large area, the temperature must be raised to 600.degree. C. or above for crystallizing. Accordingly, it is difficult to apply it to a glass

substrate or to any low-cost substrate. Another example is crystallized silicon obtained by a technique of depositing an amorphous silicon layer on a glass substrate or other substrate made of a material, such as a quartz substrate, and crystallizing it by a heat treatment at 550.degree. C. to 650.degree. C. This technique has made remarkable progress in recent years. This technique is also considered to be promising, since it can be applied to various substrate materials because crystallization of silicon can be realized at low temperature. However, since this technique requires a heating process at a temperature of 550.degree. C. to 650.degree. C., a crystallization rate of silicon is low and a film thickness is small. This technique also cannot

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